



# DCR690G52

# **Phase Control Thyristor**

DS5830-4 August 2014 (LN31837)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR690G52* DCR690G50 DCR690G48	5200 5000 4800	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to }125^{\circ}\text{C},\\ I_{DRM} &= I_{RRM} = 100\text{mA},\\ V_{DRM}, V_{RRM}  t_p &= 10\text{ms},\\ V_{DSM}  \&  V_{RSM} &= \\ V_{DRM}  \&  V_{RRM} + 100V\\ respectively \end{split}$

Lower voltage grades available. \* 5000V @ -40°C, 5200V @ 0°C

## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR690G52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

#### **KEY PARAMETERS**

 $\begin{array}{lll} V_{DRM} & 5200V \\ I_{T(AV)} & 690A \\ I_{TSM} & 9450A \\ dV/dt^* & 1500V/\mu s \\ dI/dt & 300A/us \end{array}$ 

## \* Higher dV/dt selections available

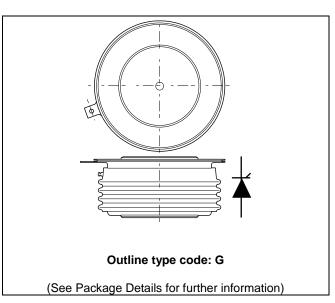


Fig. 1 Package outline



## **CURRENT RATINGS**

## $T_{case} = 60$ °C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units		
Double Si	Double Side Cooled					
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load		Α		
I <sub>T(RMS)</sub>	RMS value	-	1084	Α		
I <sub>T</sub>	Continuous (direct) on-state current	-	1050	Α		

## **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, T <sub>case</sub> = 125°C	9.45	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	0.45	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.0268	°C/W
		Single side cooled	Anode DC	-	0.0527	°C/W
			Cathode DC	-	0.0652	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 11.5kN	Double side	-	0.0072	°C/W
		(with mounting compound)	Single side	-	.0144	°C/W
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			10	13	kN





## **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, gate open		-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	150	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	300	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
V <sub>T(TO)</sub>	Threshold voltage – Low level	100A to 380A at T <sub>case</sub> = 125°C		-	.9	V
	Threshold voltage – High level	380A to 3000A at T <sub>case</sub> = 125°C		-	1.075	V
r <sub>T</sub>	On-state slope resistance – Low level	100A to 380A at T <sub>case</sub> = 125°C		-	1.618	mΩ
	On-state slope resistance – High level	380A to 3000A at T <sub>case</sub> = 125°C		-	1.125	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 5$ A/ $\mu$ s,		400	800	μs
		dV <sub>DR</sub> /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$ , $T_j = 125$ °C, $dI/dt = 5A/\mu s$ ,		1200	2400	μC
ΙL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA



## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

### **CURVES**

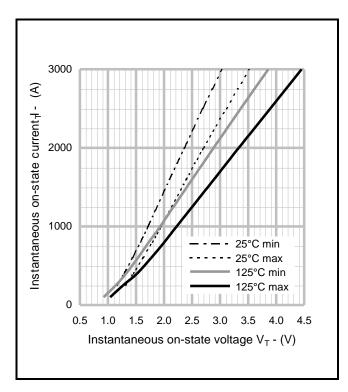


Fig.2 Maximum & minimum on-state characteristics

**V<sub>TM</sub> EQUATION** 

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.246536B = 0.166331

C = 0.00331

D = -0.008349

these values are valid for  $T_j = 125$ °C for  $I_T 50$ A to 3000A

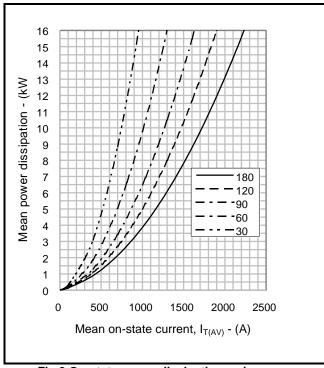


Fig.3 On-state power dissipation – sine wave

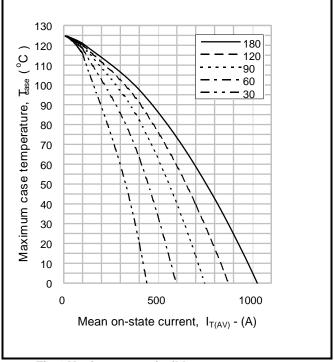


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

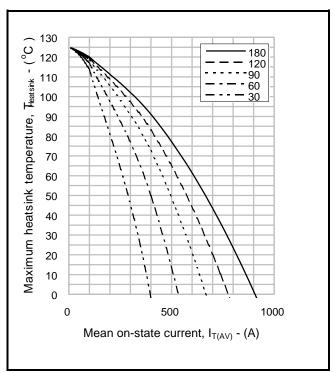


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

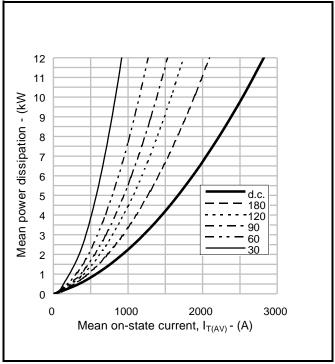


Fig.6 On-state power dissipation – rectangular wave

2.1488

1.8248

4.582

4.2295

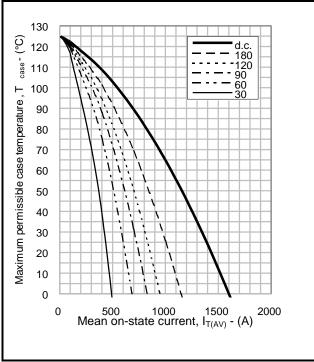


Fig.7 Maximum permissible case temperature, double side cooled - rectangular wave

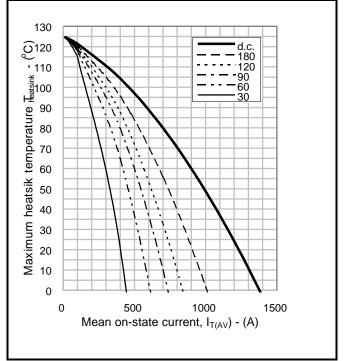


Fig.8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

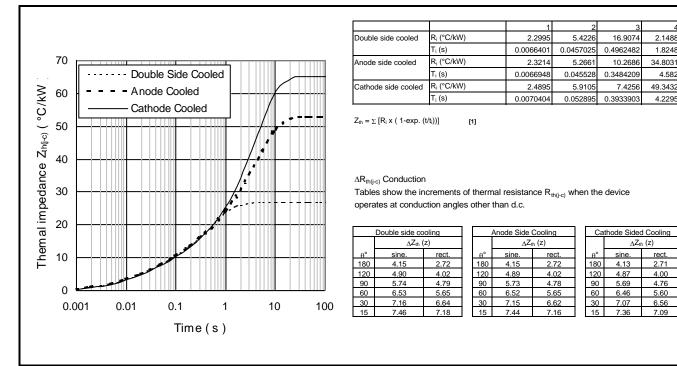
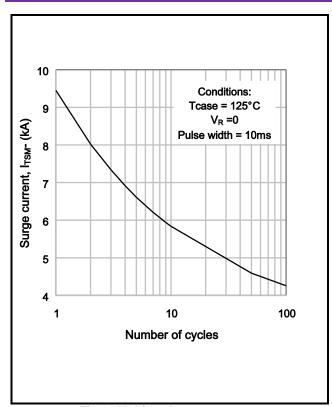


Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)



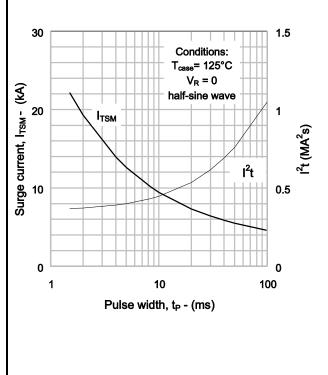
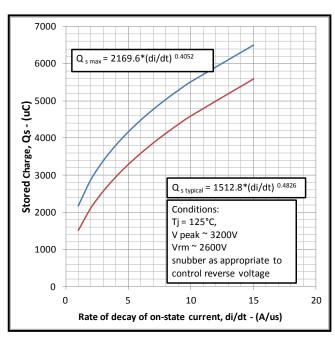
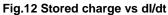


Fig.10 Multi-cycle surge current

Fig.11 Single-cycle surge current





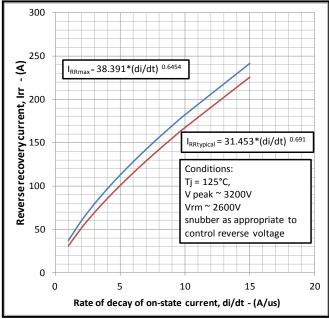


Fig.13 Reverse recovery current vs dl/dt

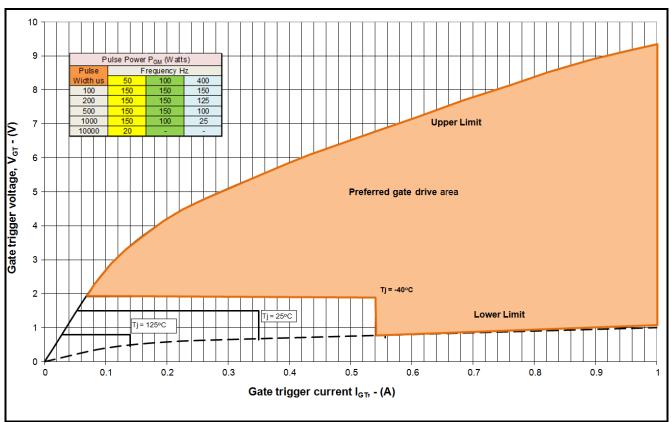


Fig14 Gate Characteristics

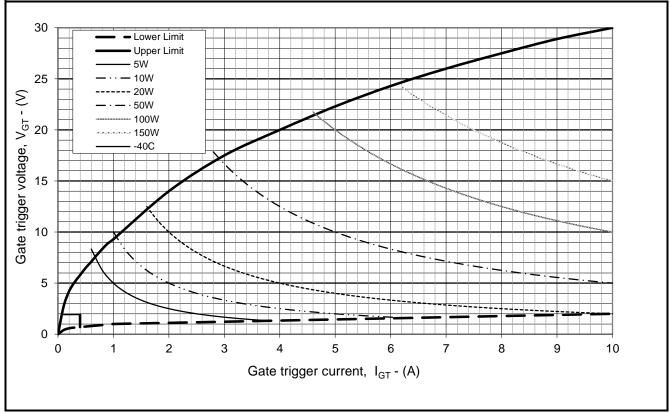


Fig. 15 Gate characteristics





#### PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

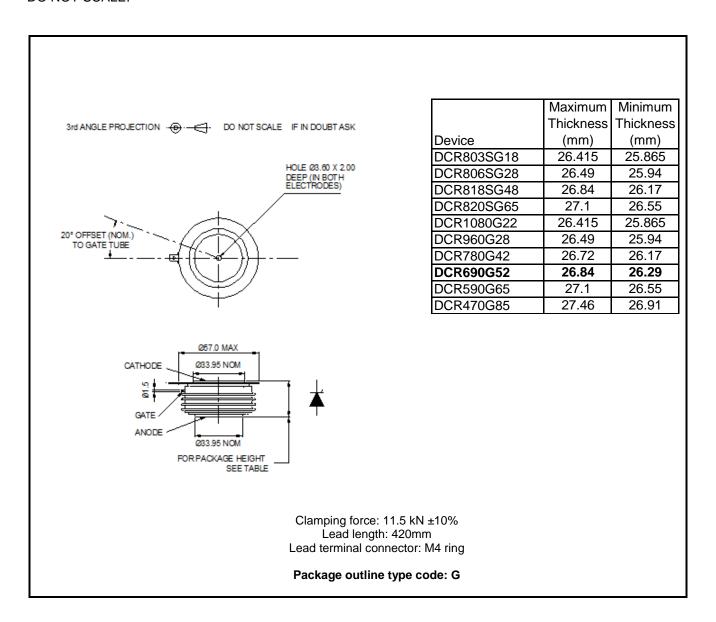


Fig.16 Package outline





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